

P4KE Transient Voltage Suppressor Diode Series

Bipolar

General Information

The P4KE series is designed to protect voltage sensitive components from high voltage, high energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. The P4KE series is supplied in YINT Semiconductor's exclusive, cost-effective, highly reliable and is ideally suited for use in communication systems, automotive, numerical controls , process controls, medical equipment, business machines, power supplies and many other industrial/consumer Applications.

Features

- Glass passivated chip
- 400W peak pluse power capability with a 10/1000 µ s waveform,rapetitive rate(duty cycle):0.01%
- Low leakage
- Uni and Bidirectional unit
- Excellent clamping capability
- Very fast response time
- RoHS compliant

Mechanical Data

- Case:Molded plastic
- Epoxy:UL 94V-0 rate flame retardant
- Lead: Solderable Per MIL-STD-202,method 208 guranteed
- Polarity:Color band denotes cathode end except

DO-41

Electrical Characteristics (@ TA = 25°C Unless Otherwise Noted)						
Parameter	Symbol	Value	Unit			
Peak pulse power dissipation with a 10/1000 µs waveform	Ррк	400	Watts			
Peak pulse current with a 10/1000 µs waveform	IFSM	See next table	Amps			
Power dissipation on infinite heat sink at TL= 75 $^{\circ}$ C	PD	1	Watts			
Peak forward surge current 8.3 ms single half sine-wave	I _{FSM}	40	Amps			
Instantaneous forward voltage at 100 A for Unidirectional only	V _F	3.5/5.0	V			
Operating junction and storage temperature range	T _J ,T _{STG}	-55 to +150	°C			

Notes :

(1) Non-repetitive current pulse, per fig.5 and derated above $T_A = 25 \text{ °C}$ per fig. 2

(2) Measured 8.3 ms single half sine-wave or equivalent square wave, duty cycle = 4 pulses per minute maximum

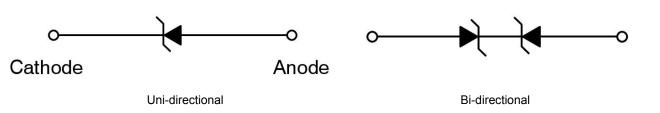
(3) V_F<3.5V for devices of V_{BR}< 200V and V_F < 5.0V for devices of V_{BR}> 201V.



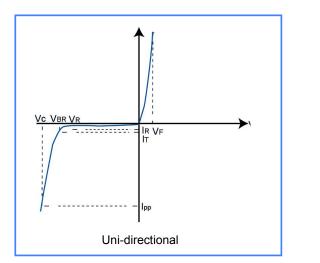
Electrical Characteristics

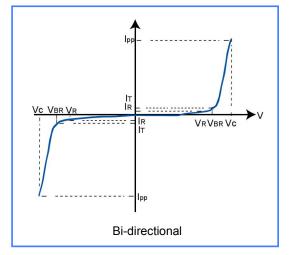
Part Number (Bi)	Part Number (Uni)	Reverse Stand off Voltage V _R (Volts)	Volta	kdown ge V _{BR} s)@I⊤ Max .V	Test Current Ιτ(mA)	Maximum Reverse Leakage I _R @ V _R (µA)	Maximum Peak Pulse Current I pp (A)	Maximum Clamping Voltage V _C @ I _{pp} (V)
P4KE33CA	P4KE33A	28.2	31.35	34.65	1	5	8.75	45.7

Functional Diagram



I-V Curve Characteristics



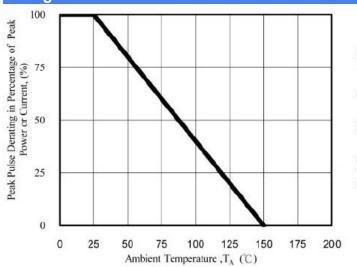


Symbol	Parameter	
Ipp	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
V _{RWM}	Working Peak Reverse Voltage	
I R	Maximum Reverse Leakage Current @V RWM	
V BR	Breakdown Voltage @ I⊤	
Ιτ	Test Current	



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Rating & Characteristic Curves





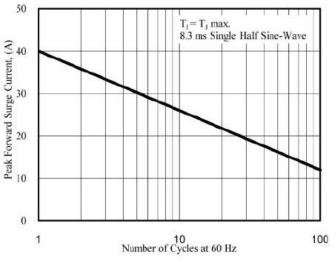


Fig. 2 - Maximum Non-Repetitive Surge Current

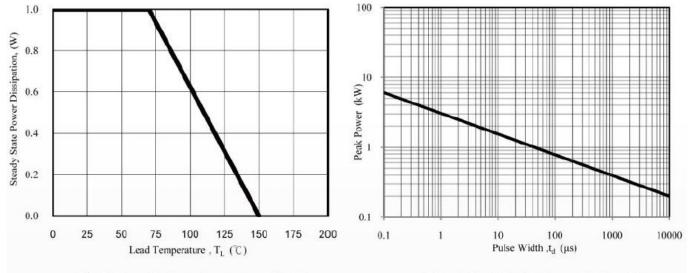
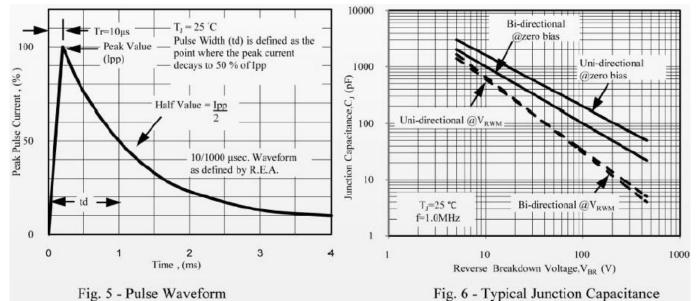


Fig. 3 - Steady State Power Derating Curve





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Disclaimer

Specifications are subject to change without notice.

The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.

Users should verify actual device performance in their specific applications.